

IN THE CLAIMS

Please amend the Claims as follows:

B¹

5. (AMENDED) The method according to Claim 1 wherein said silicon ions are implanted into said low dielectric constant material layer to a depth of between about 50 and 600 Angstroms thereby forming a roughened silicon-implanted surface of said low dielectric constant material layer.

B²

16. (AMENDED) The method according to Claim 12 wherein said silicon ions are implanted into said first and second low dielectric constant material layers to a depth of between about 50 and 600 Angstroms thereby forming a roughened silicon-implanted surface of said first and second low dielectric constant material layers.